

GBJ25005 - GBJ2510

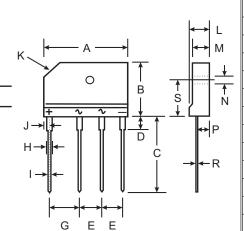
25A GLASS PASSIVATED BRIDGE RECTIFIER

Features

- Glass Passivated Die Construction
- High Case Dielectric Strength of 1500V_{RMS}
- Low Reverse Leakage Current
- Surge Overload Rating to 350A Peak
- Ideal for Printed Circuit Board Applications
- **UL Listed Under Recognized Component** Index, File Number E94661
- Lead Free Finish/RoHS Compliant (Note 4)

Mechanical Data

- Case: GBJ
- Case Material: Molded Plastic. UL Flammability Classification 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Lead Free Plating (Tin Finish).
- Polarity: Molded on Body
- Mounting: Through Hole for #6 Screw
- Mounting Torque: 5.0 in-lbs Maximum
- Marking: Type Number
- Weight: 6.6 grams (approximate)



GBJ					
Dim	Min	Max			
Α	29.70	30.30			
В	19.70	20.30			
С	17.00	18.00			
D	3.80	4.20			
E	7.30	7.70			
G	9.80	10.20			
Н	2.00	2.40			
I	0.90	1.10			
J	2.30	2.70			
K	3.0 X 45°				
L	4.40	4.80			
М	3.40	3.80			
N	3.10	3.40			
Р	2.50	2.90			
R	0.60	0.80			
S	10.80	11.20			
All Dimensions in mm					

Maximum Ratings and Electrical Characteristics @ TA = 25°C unless otherwise specified

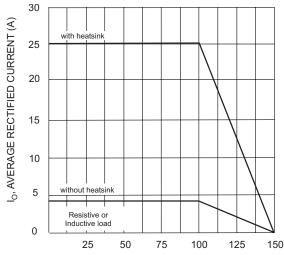
Single phase, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	GBJ 25005	GBJ 2501	GBJ 2502	GBJ 2504	GBJ 2506	GBJ 2508	GBJ 2510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Forward Rectified Output Current (Note 1) @ T _C = 100°C	Io			•	25				Α
Non-Repetitive Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}				350				Α
Forward Voltage (per element) @ I _F = 12.5A	V _{FM}				1.05				V
Peak Reverse Current	I _R				10 500				μА
I ² t Rating for Fusing (t < 8.3ms) (Note 1)		510					A ² s		
Typical Total Capacitance (per element) (Note 2)		85					pF		
Typical Thermal Resistance Junction to Case (Note 3)		0.6					°C/W		
Operating and Storage Temperature Range		-65 to +150				°C			

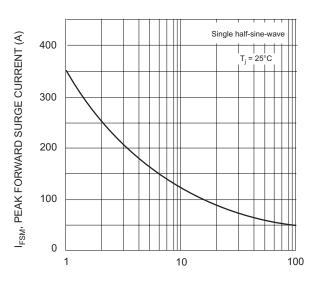
Notes:

- 1. Non-repetitive, for t > 1ms and < 8.3 ms.
- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.
- 3. Thermal resistance from junction to case per element. Unit mounted on 220 x 220 x 1.6mm aluminum plate heat sink.
- 4. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 5 and 7.

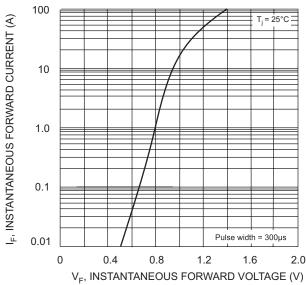




T_C, CASE TEMPERATURE (°C) Fig. 1 Forward Current Derating Curve



NUMBER OF CYCLES AT 60 Hz Fig. 3 Maximum Non-Repetitive Surge Current



V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics (per element)

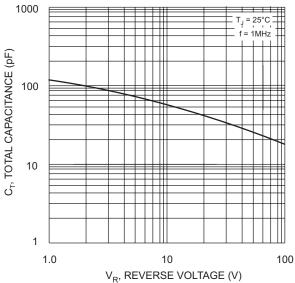
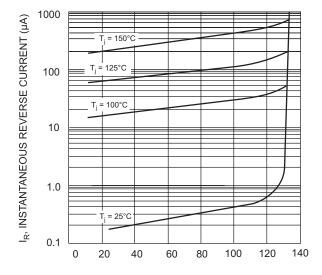


Fig. 4 Typical Total Capacitance, Per Element



PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 5 Typical Reverse Characteristics



Ordering Information (Note 5)

Device	Packaging	Shipping		
GBJ25005-F	GBJ	15/Tube		
GBJ2501-F	GBJ	15/Tube		
GBJ2502-F	GBJ	15/Tube		
GBJ2504-F	GBJ	15/Tube		
GBJ2506-F	GBJ	15/Tube		
GBJ2508-F	GBJ	15/Tube		
GBJ2510-F	GBJ	15/Tube		

Notes: 5. For packaging details, visit our website at http://www.diodes.com/datasheets/ap02008.pdf.

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